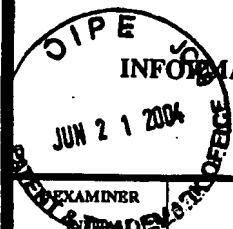
		Docket Number (Optional) <b>31550-1001</b>		Application Number <b>10/799,905</b>	
		Applicant(s) <b>Thomas J. O'Keefe, et al.</b>			
		Filing Date <b>March 12, 2004</b>		Group Art Unit <b>1762 1753</b>	
		OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
ML		"Spontaneous, Non-Aqueous Electrochemical Deposition of Copper and Palladium on Al and Al(Cu) Thin Films," R. Fang, H. Gu, J. O'Keefe and T.J. O'Keefe, University of Missouri-Rolla, Dept. of Metallurgical Engineering and Materials Research Center; W-S. Shih, Brewer Science, Inc.; K.D. Leedy and R. Cortez, Air Force Research Laboratory, Sensors Directorate			
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EXAMINER <b>William Leader</b>		DATE CONSIDERED <b>7/3/2007</b>			
<p>*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>					



## INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

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Applicant(s)

Thomas J. O'Keefe, et al.

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				Complete if Known <b>Application Number</b> 10/799,905 <b>Filing Date</b> March 12, 2004 <b>First Named Inventor</b> O'Keefe et al. <b>Art Unit</b> 1762 1753 <b>Examiner Name</b> N/A	
Sheet	1	of	2	Attorney Docket No: 31550-1001	

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>   (Use as many sheets as necessary)				<b>Complete if Known</b> <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%;">Application Number</td> <td>10/799,905</td> </tr> <tr> <td>Filing Date</td> <td>March 12, 2004</td> </tr> <tr> <td>First Named Inventor</td> <td>O'Keefe et al.</td> </tr> <tr> <td>Art Unit</td> <td>1762 1753</td> </tr> <tr> <td>Examiner Name</td> <td>N/A</td> </tr> </table>		Application Number	10/799,905	Filing Date	March 12, 2004	First Named Inventor	O'Keefe et al.	Art Unit	1762 1753	Examiner Name	N/A
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Art Unit	1762 1753														
Examiner Name	N/A														
Sheet	2	of	2	Attorney Docket No: 31550-1001											

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>2</sup>
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